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# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

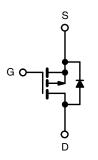


| PRODUCT SUMMARY                                   |        |  |  |  |  |
|---------------------------------------------------|--------|--|--|--|--|
| V <sub>DS</sub> (V)                               | -40    |  |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$  | 0.0115 |  |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$ | 0.0150 |  |  |  |  |
| I <sub>D</sub> (A)                                | -50    |  |  |  |  |
| Configuration                                     | Single |  |  |  |  |
| Package                                           | TO-252 |  |  |  |  |

#### **FEATURES**

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





P-Channel MOSFET

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted) |                          |                                   |             |                                       |  |
|----------------------------------------------------------------------------------|--------------------------|-----------------------------------|-------------|---------------------------------------|--|
| PARAMETER                                                                        |                          | SYMBOL                            | LIMIT       | UNIT                                  |  |
| Drain-source voltage                                                             |                          | $V_{DS}$                          | -40         | V                                     |  |
| Gate-source voltage                                                              |                          | V <sub>GS</sub> ± 20              | ± 20        | V                                     |  |
| Continuous drain current                                                         | T <sub>C</sub> = 25 °C a | 1                                 | -50         |                                       |  |
| Continuous drain current                                                         | T <sub>C</sub> = 125 °C  | - I <sub>D</sub>                  | -31         |                                       |  |
| Continuous source current (diode conduction) <sup>a</sup>                        |                          | I <sub>S</sub>                    | -50         | Α                                     |  |
| Pulsed drain current <sup>b</sup>                                                |                          | I <sub>DM</sub>                   | -180        |                                       |  |
| Single pulse avalanche current                                                   | L = 0.1 mH               | I <sub>AS</sub>                   | -27         |                                       |  |
| Single pulse avalanche energy                                                    | L = 0.1 IIII             | E <sub>AS</sub>                   | 36.4        | mJ                                    |  |
| Maximum power dissipation <sup>b</sup>                                           | T <sub>C</sub> = 25 °C   | P <sub>D</sub>                    | 62          | W                                     |  |
|                                                                                  | T <sub>C</sub> = 125 °C  |                                   | 20          | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ |  |
| Operating junction and storage temperature range                                 |                          | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C                                    |  |

| THERMAL RESISTANCE RATINGS |                       |            |       |      |  |  |
|----------------------------|-----------------------|------------|-------|------|--|--|
| PARAMETER                  |                       | SYMBOL     | LIMIT | UNIT |  |  |
| Junction-to-ambient        | PCB mount c           | $R_{thJA}$ | 50    | °C/W |  |  |
| Junction-to-case (drain)   | ction-to-case (drain) |            | 2.4   | C/VV |  |  |

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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| PARAMETER                                     | SYMBOL                 | TEST CONDITIONS                                                                                 |                                                                        | MIN. | TYP.   | MAX.   | UNIT |  |
|-----------------------------------------------|------------------------|-------------------------------------------------------------------------------------------------|------------------------------------------------------------------------|------|--------|--------|------|--|
| Static                                        |                        |                                                                                                 |                                                                        |      |        |        |      |  |
| Drain-source breakdown voltage                | $V_{DS}$               | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$                                                  |                                                                        | -40  | -      | -      | V    |  |
| Gate-source threshold voltage                 | V <sub>GS(th)</sub>    | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                                                           |                                                                        | -1.5 | -2     | -2.5   | V    |  |
| Gate-source leakage                           | I <sub>GSS</sub>       | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                                               |                                                                        | -    | -      | ± 100  | nA   |  |
|                                               |                        | V <sub>GS</sub> = 0 V                                                                           | V <sub>DS</sub> = -40 V                                                | -    | -      | -1     |      |  |
| Zero gate voltage drain current               | I <sub>DSS</sub>       | V <sub>GS</sub> = 0 V                                                                           | V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C                       | =    | -      | -50    | μΑ   |  |
|                                               |                        | V <sub>GS</sub> = 0 V                                                                           | V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C                       | -    | -      | -250   |      |  |
| On-state drain current <sup>a</sup>           | I <sub>D(on)</sub>     | V <sub>GS</sub> = -10 V                                                                         | $V_{DS} \ge 5 \text{ V}$                                               | -30  | -      | -      | Α    |  |
|                                               |                        | V <sub>GS</sub> = -10 V                                                                         | I <sub>D</sub> = -30 A                                                 | -    | 0.0095 | 0.0115 |      |  |
| During and state was interest 2               | Б                      | V <sub>GS</sub> = -10 V                                                                         | I <sub>D</sub> = -30 A, T <sub>J</sub> = 125 °C                        | -    | -      | 0.0171 |      |  |
| Drain-source on-state resistance <sup>a</sup> | R <sub>DS(on)</sub>    | V <sub>GS</sub> = -10 V                                                                         | I <sub>D</sub> = -30 A, T <sub>J</sub> = 175 °C                        | -    | -      | 0.0203 | Ω    |  |
|                                               |                        | V <sub>GS</sub> = -4.5 V                                                                        | I <sub>D</sub> = -25 A                                                 | -    | 0.0121 | 0.0150 |      |  |
| Forward transconductance <sup>b</sup>         | 9 <sub>fs</sub>        | V <sub>DS</sub> =                                                                               | -15 V, I <sub>D</sub> = -30 A                                          | -    | 71     | -      | S    |  |
| Dynamic <sup>b</sup>                          |                        |                                                                                                 |                                                                        |      | •      |        |      |  |
| Input capacitance                             | C <sub>iss</sub>       |                                                                                                 | V <sub>DS</sub> = -25 V, f = 1 MHz                                     | -    | 4872   | 6600   |      |  |
| Output capacitance                            | C <sub>oss</sub>       | $V_{GS} = 0 V$                                                                                  |                                                                        | -    | 344    | 500    | pF   |  |
| Reverse transfer capacitance                  | C <sub>rss</sub>       | 1                                                                                               |                                                                        | -    | 316    | 450    |      |  |
| Total gate charge <sup>c</sup>                | Qg                     |                                                                                                 |                                                                        | -    | 76     | 115    |      |  |
| Gate-source charge <sup>c</sup>               | Q <sub>gs</sub>        | V <sub>GS</sub> = -10 V                                                                         | $V_{GS} = -10 \text{ V}$ $V_{DS} = -20 \text{ V}, I_D = -30 \text{ A}$ |      | 11.5   | -      | nC   |  |
| Gate-drain charge <sup>c</sup>                | Q <sub>gd</sub>        | 1                                                                                               |                                                                        | -    | 13.5   | -      | 1    |  |
| Gate resistance                               | R <sub>g</sub>         |                                                                                                 | f = 1 MHz                                                              |      | 4      | 6      | Ω    |  |
| Turn-on delay time <sup>c</sup>               | t <sub>d(on)</sub>     |                                                                                                 |                                                                        | -    | 13     | 20     |      |  |
| Rise time <sup>c</sup>                        | t <sub>r</sub>         | $V_{DD}$ = -20 V, $R_L$ = 0.7 $\Omega$ $I_D \cong$ -30 A, $V_{GEN}$ = -10 V, $R_g$ = 1 $\Omega$ |                                                                        | -    | 7      | 15     | ns   |  |
| Turn-off delay time <sup>c</sup>              | t <sub>d(off)</sub>    |                                                                                                 |                                                                        | -    | 66     | 100    |      |  |
| Fall time <sup>c</sup>                        | t <sub>f</sub>         |                                                                                                 |                                                                        | -    | 28     | 45     |      |  |
| Source-Drain Diode Ratings and Charac         | teristics <sup>b</sup> |                                                                                                 |                                                                        |      |        |        |      |  |
| Pulsed current <sup>a</sup>                   | I <sub>SM</sub>        |                                                                                                 |                                                                        | -    | -      | -180   | Α    |  |
| Forward voltage                               | $V_{SD}$               | I <sub>F</sub> = -30 A, V <sub>GS</sub> = 0 V                                                   |                                                                        | -    | -0.9   | -1.5   | V    |  |
| Body diode reverse recovery time              | t <sub>rr</sub>        | I <sub>F</sub> = -30 A, di/dt = 100 A/μs                                                        |                                                                        | -    | 43     | 90     | ns   |  |
| Body diode reverse recovery charge            | $Q_{rr}$               |                                                                                                 |                                                                        | -    | 45     | 100    | nC   |  |
| Reverse recovery fall time                    | ta                     |                                                                                                 |                                                                        | -    | 26     | -      |      |  |
| Reverse recovery rise time                    | t <sub>b</sub>         |                                                                                                 |                                                                        | -    | 17     | -      | ns   |  |
| Body diode peak reverse recovery current      | I <sub>RM(REC)</sub>   |                                                                                                 |                                                                        | -    | -2.8   | -      | Α    |  |

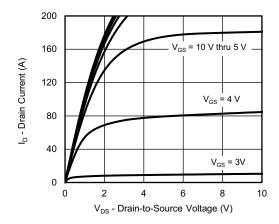
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

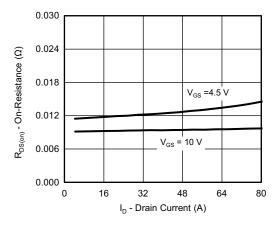
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



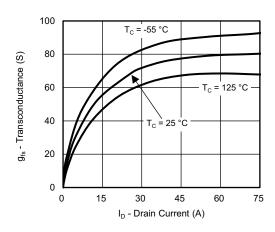
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



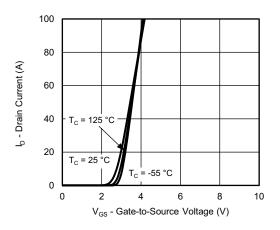
#### **Output Characteristics**



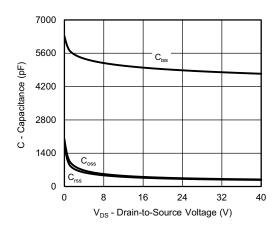
On-Resistance vs. Drain Current



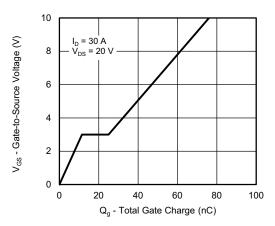
Transconductance



**Transfer Characteristics** 



Capacitance

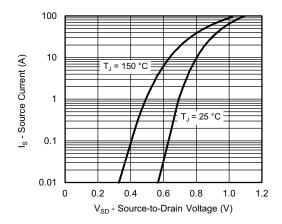


**Gate Charge** 

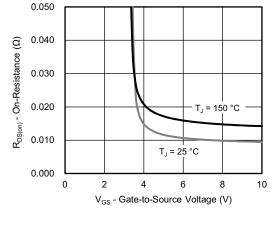
For technical questions, contact: automostechsu



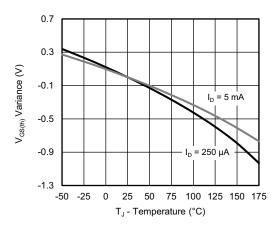
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



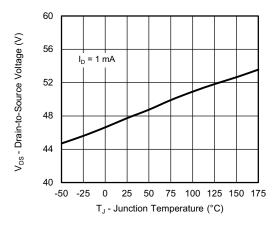
**Source Drain Diode Forward Voltage** 



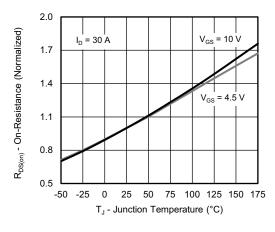
On-Resistance vs. Gate-to-Source Voltage



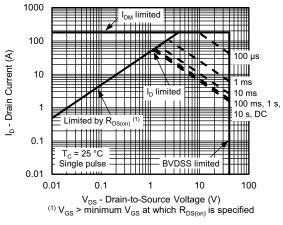
**Threshold Voltage** 



**Drain Source Breakdown vs. Junction Temperature** 



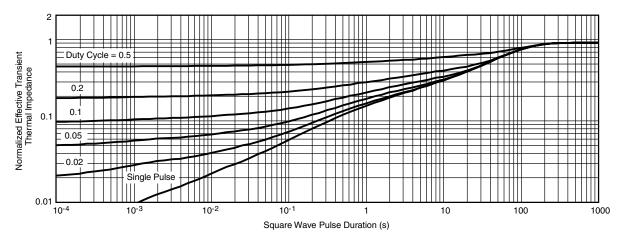
On-Resistance vs. Junction Temperature



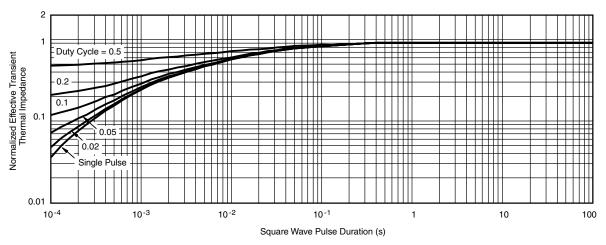
Safe Operating Area



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

### Note

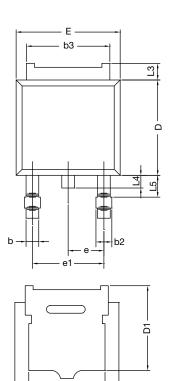
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

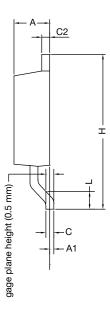
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## **TO-252AA Case Outline**





|                                              | MILLIN   | IETERS | INCHES    |       |  |
|----------------------------------------------|----------|--------|-----------|-------|--|
| DIM.                                         | MIN.     | MAX.   | MIN.      | MAX.  |  |
| Α                                            | 2.18     | 2.38   | 0.086     | 0.094 |  |
| A1                                           | -        | 0.127  | -         | 0.005 |  |
| b                                            | 0.64     | 0.88   | 0.025     | 0.035 |  |
| b2                                           | 0.76     | 1.14   | 0.030     | 0.045 |  |
| b3                                           | 4.95     | 5.46   | 0.195     | 0.215 |  |
| С                                            | 0.46     | 0.61   | 0.018     | 0.024 |  |
| C2                                           | 0.46     | 0.89   | 0.018     | 0.035 |  |
| D                                            | 5.97     | 6.22   | 0.235     | 0.245 |  |
| D1                                           | 4.10     | -      | 0.161     | -     |  |
| E                                            | 6.35     | 6.73   | 0.250     | 0.265 |  |
| E1                                           | 4.32     | -      | 0.170     | -     |  |
| Н                                            | 9.40     | 10.41  | 0.370     | 0.410 |  |
| е                                            | 2.28     | BSC    | 0.090 BSC |       |  |
| e1                                           | 4.56 BSC |        | 0.180 BSC |       |  |
| L                                            | 1.40     | 1.78   | 0.055     | 0.070 |  |
| L3                                           | 0.89     | 1.27   | 0.035     | 0.050 |  |
| L4                                           | -        | 1.02   | -         | 0.040 |  |
| L5                                           | 1.01     | 1.52   | 0.040     | 0.060 |  |
| ECN: T13-0592-Rev. A, 02-Sep-13<br>DWG: 6019 |          |        |           |       |  |

#### Note

• Dimension L3 is for reference only.



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF